



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| V _{(BR)DSS} | R _{DS(ON)} Max | I _D Τ _C = +25°C |
|----------------------|-----------------------------|---|
| -40V | 9.9 m $Ω @ V_{GS} = -10V$ | -50A |
| - 4 0V | $14mΩ @ V_{GS} = -4.5V$ | -45A |

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Backlighting

Features and Benefits

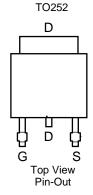
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

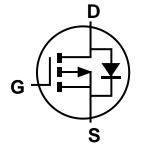
Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)



Top View





Equivalent Circuit

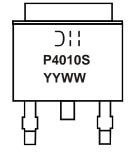
Ordering Information (Note 5)

| Part Number | Case | Packaging |
|----------------|-------|-------------------|
| DMP4010SK3Q-13 | TO252 | 2,500/Tape & Reel |

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



DII = Manufacturer's Marking
P4010S = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 15 = 2015)
WW = Week (01 to 53)



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | | |
|---|------------------|--|------------------|------------|----|
| Drain-Source Voltage | V _{DSS} | -40 | V | | |
| Gate-Source Voltage | | | V _{GSS} | ±25 | V |
| Continuous Prain Current (Note 7) V 10V | Steady State | $T_C = +25$ °C $T_C = +70$ °C | I _D | -50 -40 | А |
| Continuous Drain Current (Note 7), V _{GS} = -10V | Steady State | $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ | I _D | -15 -12 | А |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | I _{DM} | -100 | Α | | |
| Maximum Body Diode Forward Current (Note 7) | I _S | -5.5 | Α | | |
| Avalanche Current, L = 1mH (Note 8) | | | I _{AS} | -22 | Α |
| Avalanche Energy, L = 1mH (Note 8) | | | E _{AS} | 260 | mJ |

Thermal Characteristics (@ TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|--|------------------|------------------|-------------|------|
| Total Power Dissipation (Note 6) | | P_{D} | 1.7 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | R _{θJA} | 73 | °C/W |
| Total Power Dissipation (Note 7) | | P _D | 3.3 | W |
| Thermal Resistance, Junction to Ambient (Note 7) Steady State | | R _{θJA} | 38 | °C/W |
| Thermal Resistance, Junction to Case | R _{0JC} | 1.0 | C/VV | |
| Operating and Storage Temperature Range | | T_J,T_STG | -55 to +150 | °C |

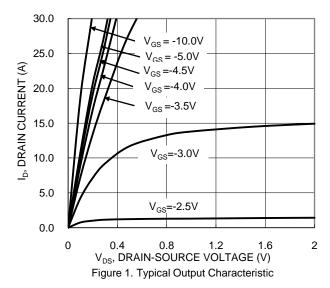
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

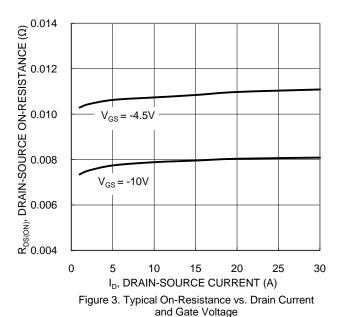
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|---|---------------------|------|------|------|-------|--|--|
| OFF CHARACTERISTICS (Note 9) | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -40 | _ | _ | V | $V_{GS} = 0V, I_{D} = -250\mu A$ | |
| Zero Gate Voltage Drain Current | I _{DSS} | | _ | -1 | μΑ | $V_{DS} = -40V, V_{GS} = 0V$ | |
| Gate-Source Leakage | I _{GSS} | | _ | ±100 | nA | $V_{GS} = \pm 25V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 9) | | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | -1.5 | -2 | -2.5 | V | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$ | |
| Static Drain-Source On-Resistance | | | 7.5 | 9.9 | mΩ | $V_{GS} = -10V, I_D = -9.8A$ | |
| Static Drain-Source On-Resistance | R _{DS(ON)} | | 10.5 | 14 | 11122 | $V_{GS} = -4.5V, I_D = -9.8A$ | |
| Diode Forward Voltage | V_{SD} | _ | -0.7 | -1 | V | $V_{GS} = 0V, I_{S} = -1A$ | |
| DYNAMIC CHARACTERISTICS (Note 10) | | | | | | | |
| Input Capacitance | Ciss | | 4234 | _ | | $V_{DS} = -20V$, $V_{GS} = 0V$ f = 1MHz | |
| Output Capacitance | Coss | | 1036 | _ | pF | | |
| Reverse Transfer Capacitance | C _{rss} | _ | 526 | _ | | | |
| Gate Resistance | Rg | | 7.8 | _ | Ω | $V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$ | |
| Total Gate Charge (V _{GS} = -4.5V) | Q_g | _ | 42.7 | _ | | | |
| Total Gate Charge (V _{GS} = -10V) | Qg | _ | 91 | _ | nC | $V_{DS} = -20V,$ $I_{D} = -9.8A$ | |
| Gate-Source Charge | Qgs | _ | 14.2 | _ | IIC | | |
| Gate-Drain Charge | Q_{gd} | _ | 13.5 | _ | | | |
| Turn-On Delay Time | t _{D(ON)} | _ | 13.2 | _ | | $V_{GS} = -10V, V_{DD} = -20V,$ $R_{G} = 6\Omega, I_{D} = -1A$ | |
| Turn-On Rise Time | t _R | | 10 | _ | | | |
| Turn-Off Delay Time | t _{D(OFF)} | _ | 303 | _ | ns | | |
| Turn-Off Fall Time | t _F | _ | 138 | _ | | | |
| Reverse Recovery Time | t _{RR} | _ | 26 | _ | ns | $I_F = -9.8A$, $di/dt = -100A/\mu s$ | |
| Reverse Recovery Charge | Q _{RR} | _ | 20 | _ | nC | $I_F = -9.8A$, $di/dt = -100A/\mu s$ | |

Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.







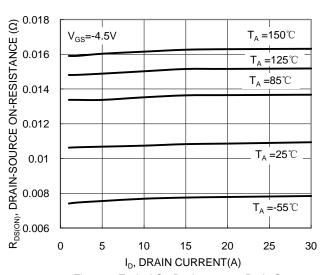
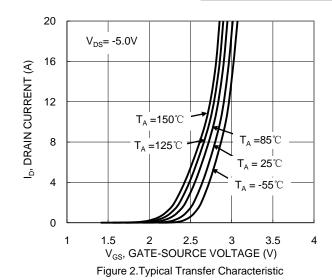
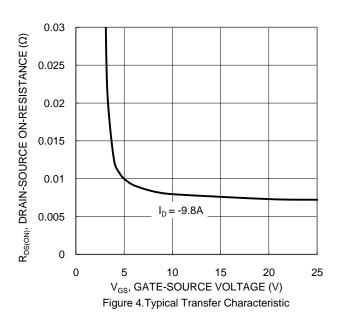


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





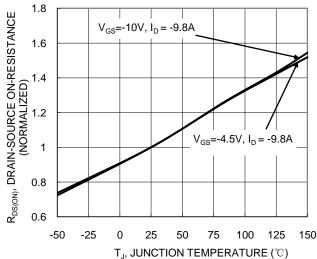
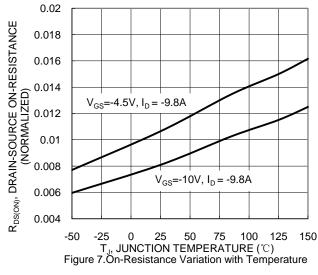
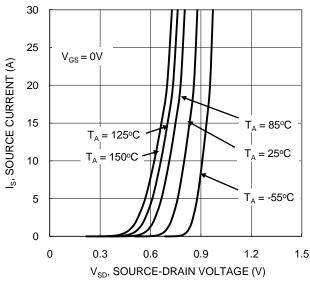
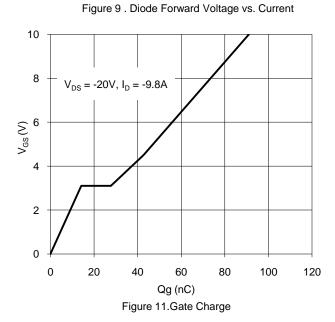


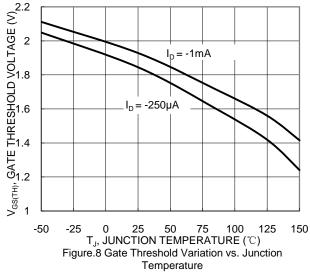
Figure 6.On-Resistance Variation with Temperature











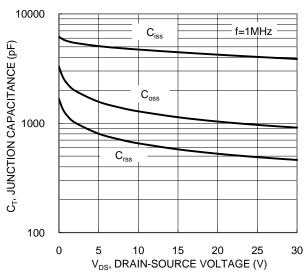
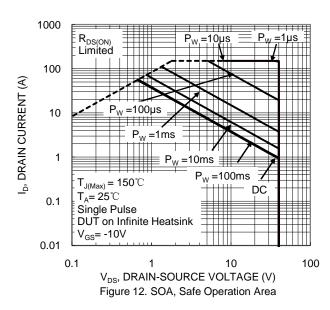


Figure 10. Typical Junction Capacitance





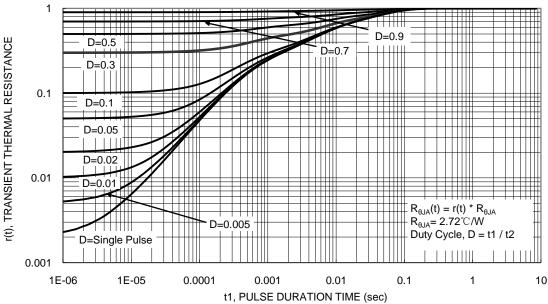


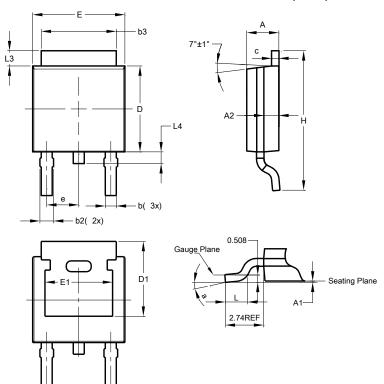
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

TO252 (DPAK)

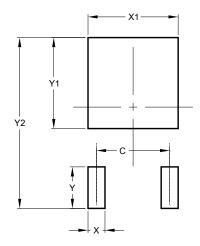


| TO252 (DPAK) | | | | | |
|----------------------|------|-------|-------|--|--|
| Dim | Min | Max | Тур | | |
| Α | 2.19 | 2.39 | 2.29 | | |
| A1 | 0.00 | 0.13 | 0.08 | | |
| A2 | 0.97 | 1.17 | 1.07 | | |
| b | 0.64 | 0.88 | 0.783 | | |
| b2 | 0.76 | 1.14 | 0.95 | | |
| b3 | 5.21 | 5.46 | 5.33 | | |
| С | 0.45 | 0.58 | 0.531 | | |
| D | 6.00 | 6.20 | 6.10 | | |
| D1 | 5.21 | - | - | | |
| е | - | - | 2.286 | | |
| Е | 6.45 | 6.70 | 6.58 | | |
| E1 | 4.32 | - | - | | |
| Н | 9.40 | 10.41 | 9.91 | | |
| L | 1.40 | 1.78 | 1.59 | | |
| L3 | 0.88 | 1.27 | 1.08 | | |
| L4 | 0.64 | 1.02 | 0.83 | | |
| а | 0° | 10° | - | | |
| All Dimensions in mm | | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

TO252 (DPAK)



| Dimensions | Value (in mm) | | |
|------------|---------------|--|--|
| С | 4.572 | | |
| Х | 1.060 | | |
| X1 | 5.632 | | |
| Y | 2.600 | | |
| Y1 | 5.700 | | |
| Y2 | 10.700 | | |



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